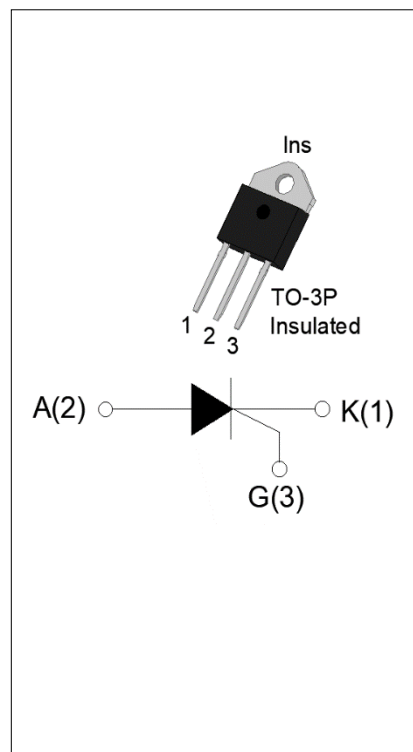




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1675Z SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, UPS, SVC, power charger, T-tools etc. JCT1675Z provide a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	75	A
V_{DRM}/V_{RRM}	1600	V
I_{GT}	10-80	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1600	V
Average on-state current ($T_c \leq 50^\circ\text{C}$)	$I_{T(AV)}$	48	A
RMS on-state current ($T_c \leq 50^\circ\text{C}$)	$I_{T(RMS)}$	75	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	1000	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}$, $T_j=25^\circ\text{C}$)		1100	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	5000	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	200	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	12	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	10	-	80	mA
V_{GT}		-	-	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3K\Omega$	0.25	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	250	mA
I_H	$I_T=500mA$	-	-	200	mA
dV/dt	$V_D=1070V$ Gate Open $T_j=125^\circ C$	2000	-	-	V/ μs
t_{on}	$I_G=100mA$ $I_A=1A$ $I_R=100mA$ $T_j=25^\circ C$	-	8	-	μs
t_{off}		-	150	-	

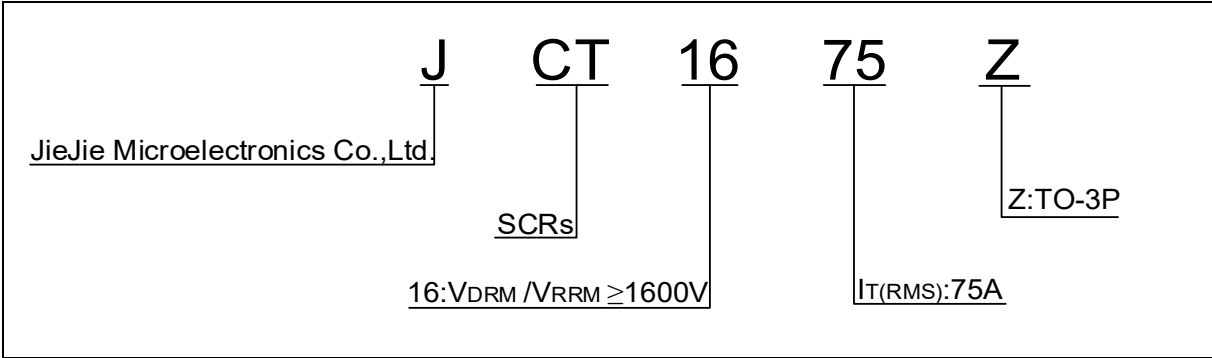
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=100A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.8	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.93	V
R_D	Dynamic resistance	$T_j=125^\circ C$	6	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	20	μA
I_{RRM}		$T_j=125^\circ C$	8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(DC)	0.7	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	50	$^\circ C/W$

ORDERING INFORMATION



MARKING

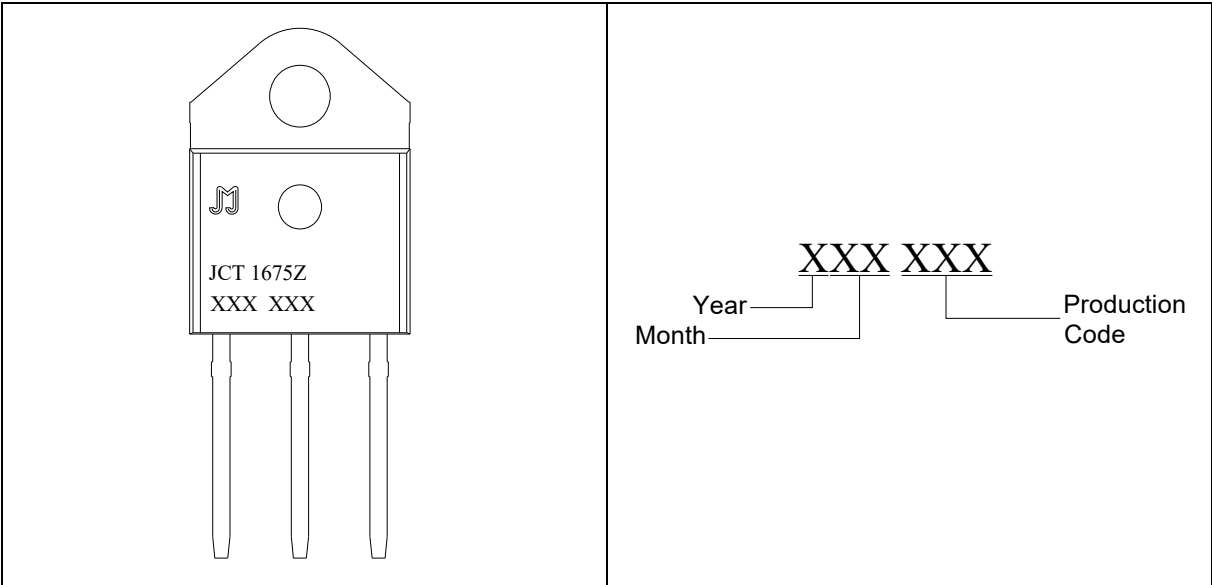


FIG.1 Maximum power dissipation versus RMS on-state current

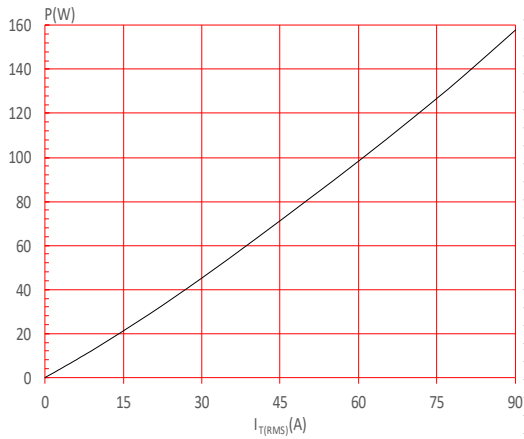


FIG.2: RMS on-state current versus case temperature

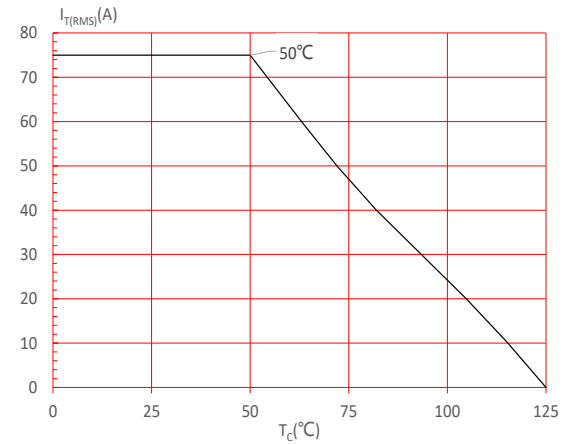


FIG.3: Surge peak on-state current versus number of cycles

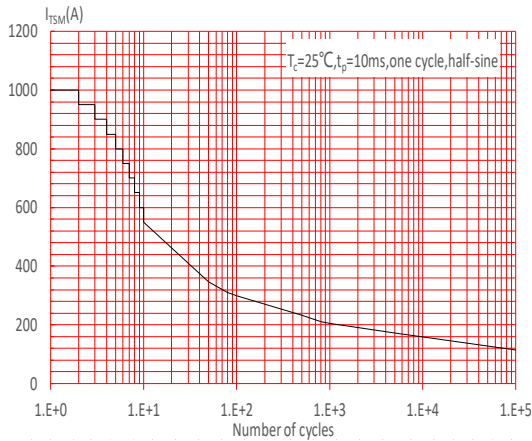


FIG.4: On-state characteristics

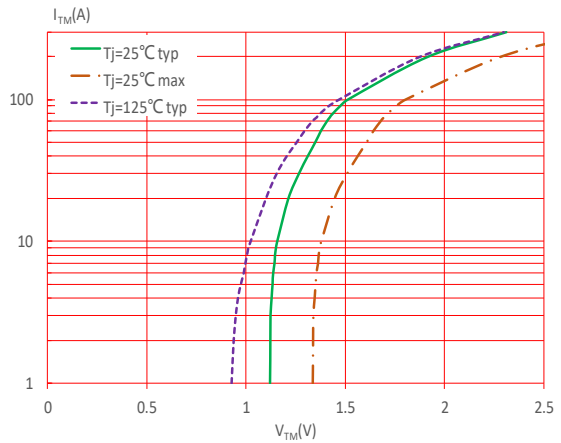


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($dI/dt < 200\text{A}/\mu\text{s}$)

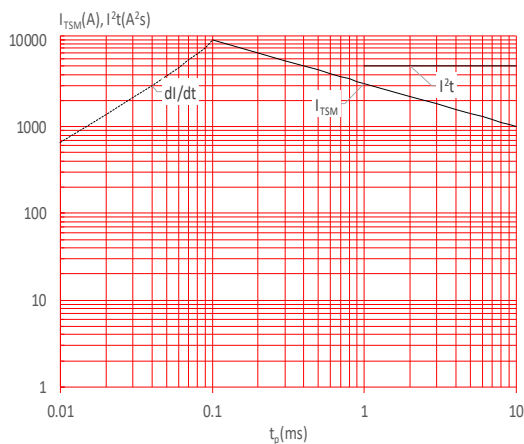


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

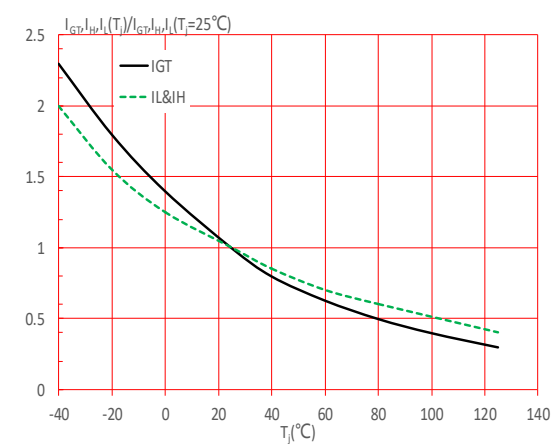
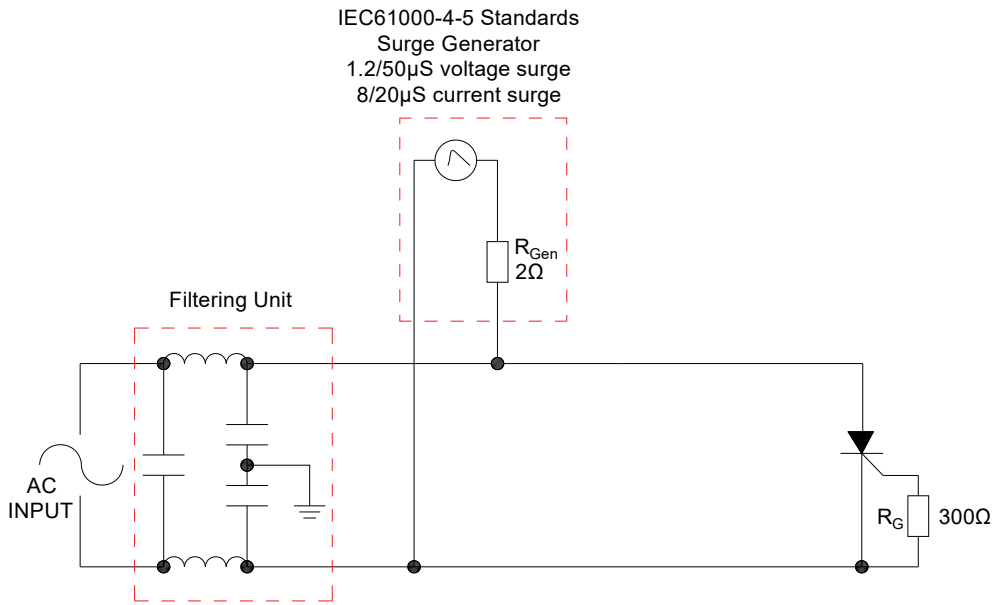


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

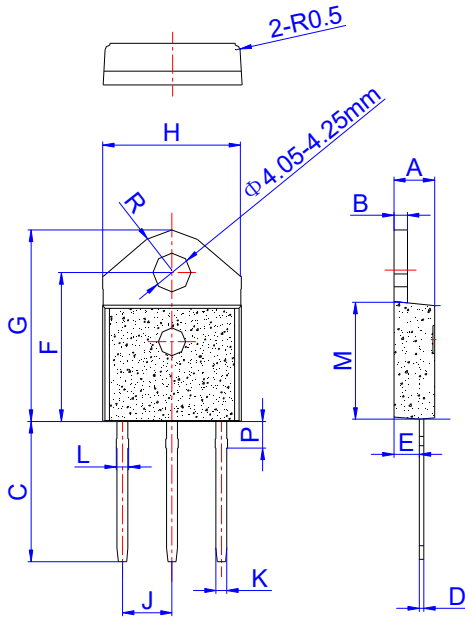
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1675Z	1600	10-80	TO-3P	30	Tube

Document Revision History

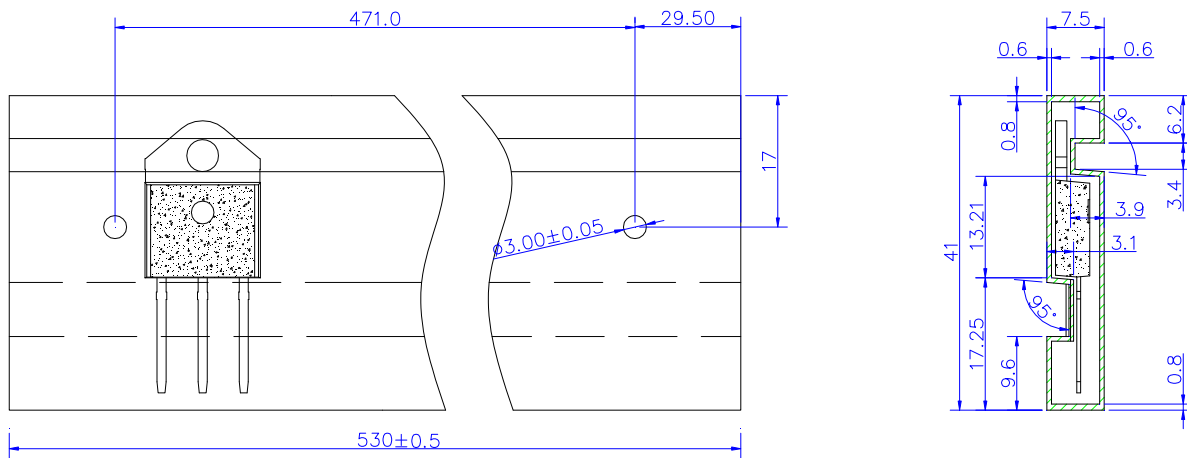
Date	Revision	Changes
May.07, 2024	A.1.0	Last update

PACKAGE MECHANICAL DATA




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250

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